

The Kawaguchi et al. patent merely discloses a p-type semiconductor substrate 11, a gate insulating film 17 and a field oxide film 18. (See FIG. 3) A gate electrode 19 spans from the gate insulating film 17 to the field oxide film 18. An n-type source layer 13 is located near the gate electrode. An n-type drain layer 16 is formed a distance from the gate electrode 19. A first n-type offset layer 14 is located around the drain layer 16. A second n-type offset layer 15 is adjacent the drain layer 16. The second n-type offset layer 15 has a higher dosage than the first n-type offset layer 14 (see column 5, lines 61-64). The first n-type offset layer 14 extends deeper into the semiconductor substrate 11 than the second n-type offset layer 15.

The Office Action appears to have interpreted the Kawaguchi et al. disclosure in two different ways to reject claim 1. As discussed below, under either interpretation, we disagree with the rejection.

According to one interpretation, the Office Action correlated Kawaguchi's first offset layer 14, second offset layer 15, and drain layer 16 to claim 1's drift region, impurities layer and drain region, respectively. Under that interpretation, the Office Action asserted that the second offset layer 15 has a higher dosage than the first offset layer 14. However, under that interpretation, the drain layer 16 is not in direct contact with the (lower dosage) first offset layer 14, as is featured in claim 1. The drain layer 16 is in direct contact with the (higher dosage) second offset layer 15.

Therefore, under that interpretation of the Kawaguchi et al. patent, claim 1 should be allowable.

According to another interpretation, the Office Action asserted that the first offset layer 14 and the second offset layer 15 collectively comprise "a drift region." By characterizing those two layers 14 and 15 as a single drift region, the Office Action concluded that the drain layer 16 is in "direct contact" with that drift region. (See page 3 of the Office Action, "the drain region is in direct contact with the drift region (15/14[]).") Under that interpretation, however, the "drift region" is not less highly doped than an impurities layer that is formed adjacent to the drain region, as is featured in claim 1. Indeed, if the two layers 14 and 15 are considered to be a single

“drift region,” then the Kawaguchi et al. patent fails to disclose an impurities region that is formed adjacent to the drain region and is more highly doped than the drift region.

Therefore, under that interpretation of the Kawaguchi et al. patent, claim 1 should be allowable.

Applicants submit that claim 1 should be allowable for at least the foregoing reasons.

Claims 2 and 3 depend from claim 1 and, therefore, should be allowable for at least the same reasons as claim 1.

Claims 8-10 also were rejected under 35 U.S.C. §102(b) as being anticipated by the Kawaguchi et al. patent.

Claim 8 recites features that are similar to the features discussed above with reference to claim 1.

Accordingly, claim 8 should be allowable for at least the same reasons as claim 1.

Claims 9 and 10 depend from claim 8 and, therefore, should be allowable for at least the same reasons as claim 8.

Claim 14 also was rejected under 35 U.S.C. §102(b) as being anticipated by the Kawaguchi et al. patent.

Claim 14 recites features that are similar to the features discussed above with reference to claim 1.

Accordingly, claim 14 should be allowable for at least the same reasons as claim 1.

It is believed that all of the pending claims have been addressed. However, the absence of a reply to a specific rejection, issue or comment does not signify agreement with or concession of that rejection, issue or comment. In addition, because the arguments made above may not be exhaustive, there may be reasons for patentability of any or all pending claims (or

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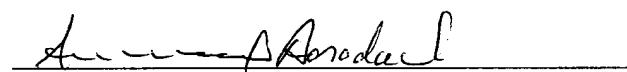
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other claims) that have not been expressed. Finally, nothing in this paper should be construed as an intent to concede any issue with regard to any claim, except as specifically stated in this paper, and the amendment of any claim does not necessarily signify concession of unpatentability of the claim prior to its amendment.

No fee is believed to be due. However, please apply any charges or credits to deposit account 06-1050.

Respectfully submitted,

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Samuel Borodach
Reg. No. 38,388

Fish & Richardson P.C.
Citigroup Center
52nd Floor
153 East 53rd Street
New York, New York 10022-4611
Telephone: (212) 765-5070
Facsimile: (212) 258-2291

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